

METHOD OF PIPING DEFECT DETECTION

Abstract

A method of piping defect detection is disclosed. First, a sample is provided. The sample has a silicon substrate, a plurality of electric devices disposed on the silicon substrate surface, a dielectric layer covering the electric devices and the substrate, and a polysilicon layer positioned on the dielectric layer, which is electrically connected to the electric devices through contact holes in the dielectric layer. A chemical mechanical polish process is performed to remove the polysilicon layer on the dielectric layer and parts of the dielectric layer. A wet etching process is then performed to delayer the dielectric layer. After that, the sample is inspected under an ultraviolet light irradiation for detecting the piping defects in the dielectric layer of the sample.